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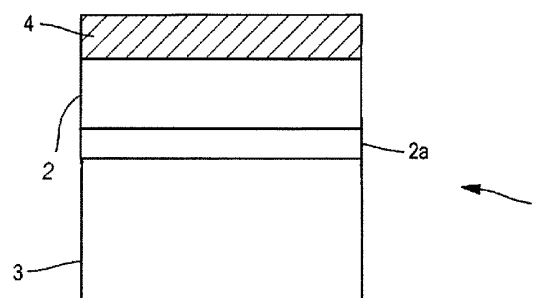


FIG. 1

(57) Abstract: The invention relates to a support (1) for a semiconductor structure, comprising a base substrate (3), a first silicon dioxide insulating layer (2a) positioned on the base substrate (3) and having a thickness greater than 20 nm, and a charge trapping layer (2) having a resistivity higher than 1000 ohm.cm and a thickness greater than 5 microns positioned on the first insulating layer (2a).



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